

## Thyristors

### SKT 600 SKT 760



V <sub>RRM</sub>	V <sub>RRM</sub> V <sub>DRM</sub>	$\left(\frac{dv}{dt}\right)_{cr}$	I <sub>TRMS</sub> (maximum values for continuous operation)	
			1400 A	1600 A
V	V	V/μs	I <sub>TAV</sub> (sin. 180; T <sub>case</sub> = ...; DSC)	
			890 A (57 °C)	1020 A (56 °C)
500	400	500	<b>SKT 600/04 D</b>	<b>SKT 760/04 D</b>
900	800	500	<b>SKT 600/08 D</b>	<b>SKT 760/08 D</b>
1300	1200	500 1000	<b>SKT 600/12 D</b> <b>SKT 600/12 E</b>	<b>SKT 760/12 D</b> <b>SKT 760/12 E</b>
1500	1400	1000	<b>SKT 600/14 E</b>	<b>SKT 760/14 E</b>
1700	1600	1000	<b>SKT 600/16 E</b>	<b>SKT 760/16 E</b>
1900	1800	1000	<b>SKT 600/18 E</b>	<b>SKT 760/18 E</b>

Symbol	Conditions	SKT 600	SKT 760
I <sub>TAV</sub>	sin. 180; (T <sub>case</sub> = ...); DSC	600 A (85 °C)	760 A (80 °C)
I <sub>TSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms T <sub>vj</sub> = 125 °C; 10 ms	11 500 A 10 000 A	15 000 A 13 000 A
i <sup>2</sup> t	T <sub>vj</sub> = 25 °C; 8,3 ... 10 ms T <sub>vj</sub> = 125 °C; 8,3 ... 10 ms	660 kA <sup>2</sup> s 500 kA <sup>2</sup> s	1125 kA <sup>2</sup> s 845 kA <sup>2</sup> s
t <sub>gd</sub>	T <sub>vj</sub> = 25 °C; I <sub>G</sub> = 1 A; di <sub>G</sub> /dt = 1 A/μs	typ. 1 μs	
t <sub>gr</sub>	V <sub>D</sub> = 0,67 · V <sub>DRM</sub>	typ. 2 μs	
(di/dt) <sub>cr</sub>	f = 50 ... 60 Hz	125 A/μs	
I <sub>H</sub>	T <sub>vj</sub> = 25 °C; typ./max.	150 mA/500 mA	
I <sub>L</sub>	T <sub>vj</sub> = 25 °C; typ./max.	500 mA/2 A	
t <sub>q</sub>	T <sub>vj</sub> = 125 °C; typ.	100 ... 200 μs	
V <sub>T</sub>	T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 2400 A; max.	2,0 V	1,65 V
V <sub>T(TO)</sub>	T <sub>vj</sub> = 125 °C	1,0 V	0,92 V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C	0,4 mΩ	0,3 mΩ
I <sub>DD</sub> , I <sub>RD</sub>	T <sub>vj</sub> = 125 °C; V <sub>DD</sub> = V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub>	80 mA	80 mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C	3 V	
I <sub>GT</sub>	T <sub>vj</sub> = 25 °C	200 mA	
V <sub>GD</sub>	T <sub>vj</sub> = 125 °C	0,25 V	
I <sub>GD</sub>	T <sub>vj</sub> = 125 °C	10 mA	
R <sub>thjc</sub>	cont. DSC	0,038 °C/W	
	sin. 180; DSC/SSC	0,040/0,082 °C/W	
	rec. 120; DSC/SSC	0,045/0,093 °C/W	
R <sub>thch</sub>	DSC/SSC	0,007/0,014 °C/W	
T <sub>vj</sub>		- 40 ... +125 °C	
T <sub>stg</sub>		- 40 ... +130 °C	
F	SI units	10 ... 13 kN	
w	US units	2200 ... 2850 lbs.	
		240 g	
Case		B 10	

### Features

- Hermetic metal cases with ceramic insulators
- Capsule packages for double sided cooling
- Shallow design with single sided cooling
- International standard cases
- Off-state and reverse voltages up to 1800 V

### Typical Applications

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)

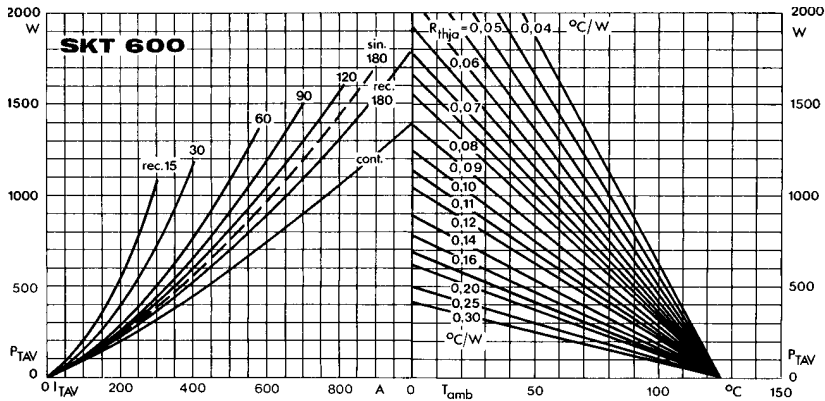


Fig. 1 a Power dissipation vs. on-state current and ambient temperature

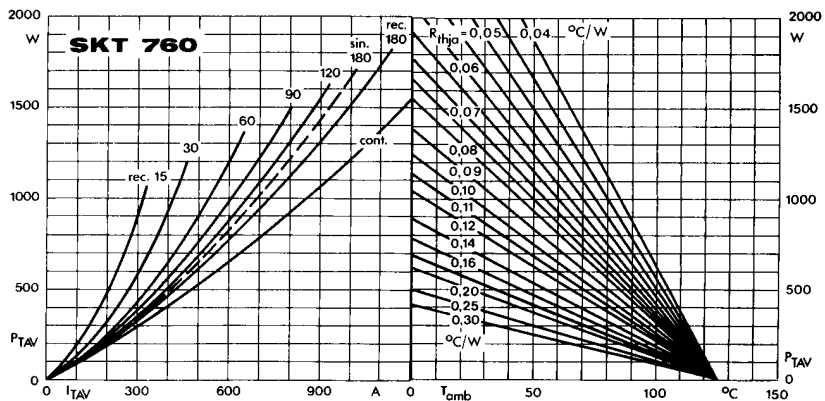


Fig. 1 b Power dissipation vs. on-state current and ambient temperature

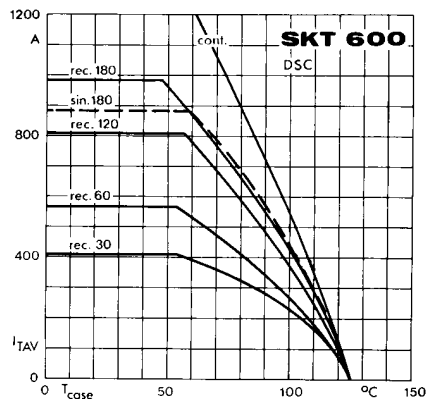


Fig. 2 a Rated on-state current vs. case temperature

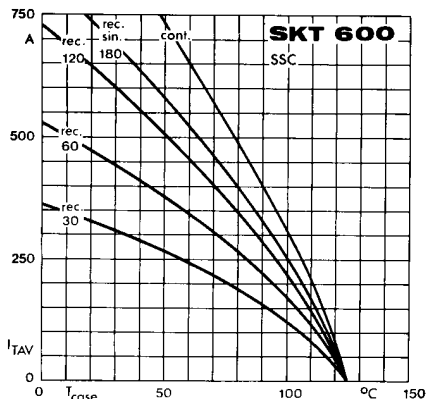


Fig. 2 b Rated on-state current vs. case temperature

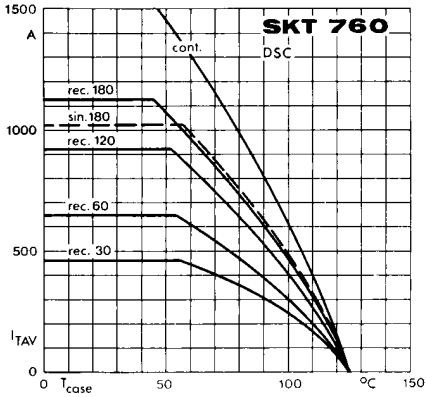


Fig. 2 c Rated on-state current vs. case temperature

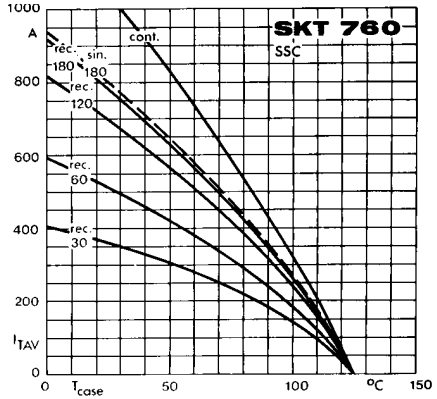


Fig. 2 d Rated on-state current vs. case temperature

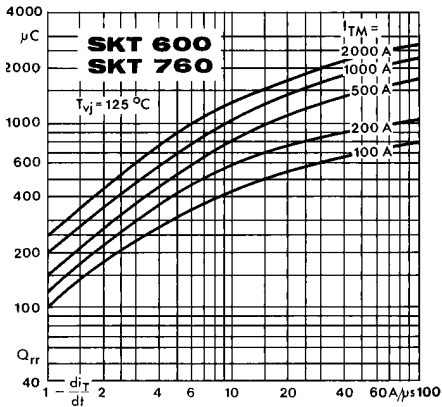


Fig. 3 Recovered charge vs. current decrease

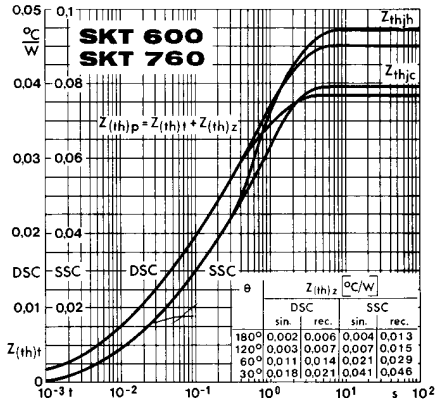


Fig. 4 Transient thermal impedance vs. time

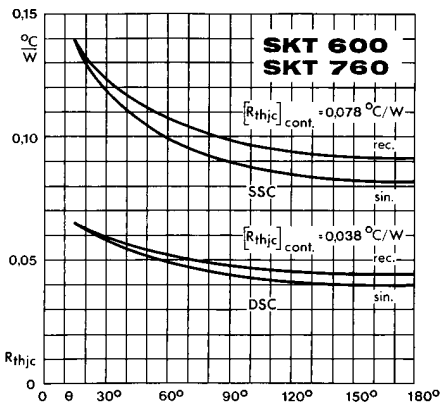


Fig. 5 Thermal resistance vs. conduction angle

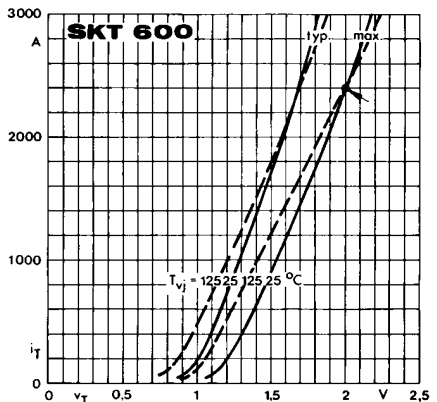


Fig. 6 a On-state characteristics

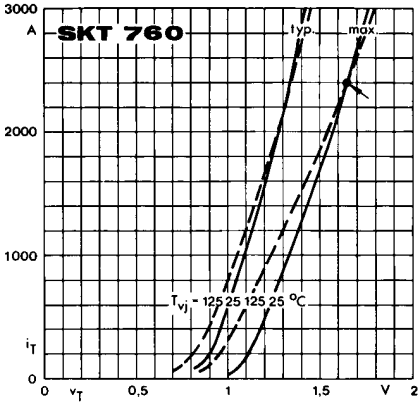


Fig. 6 b On-state characteristics

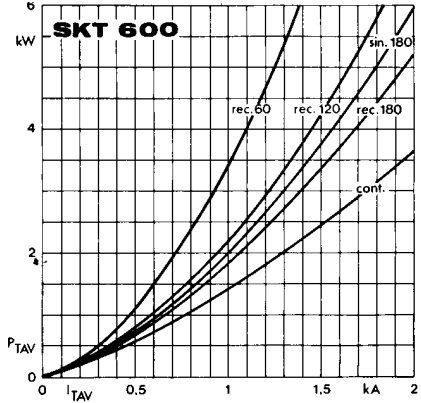


Fig. 7 a Power dissipation vs. on-state current

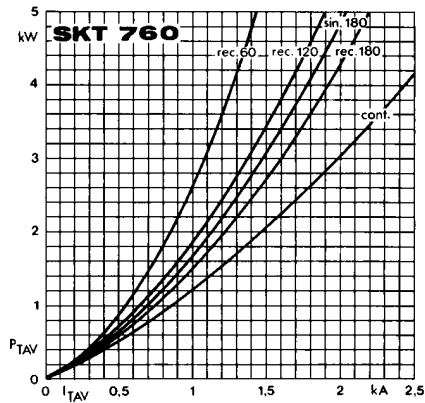


Fig. 7 b Power dissipation vs. on-state current

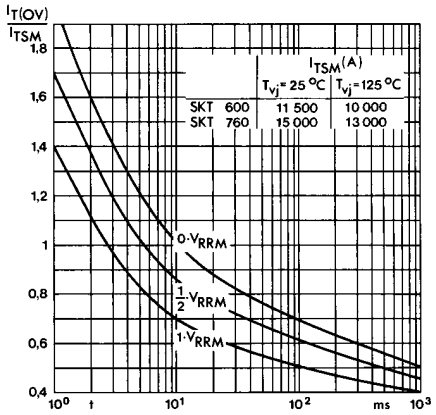


Fig. 8 Surge overload current vs. time

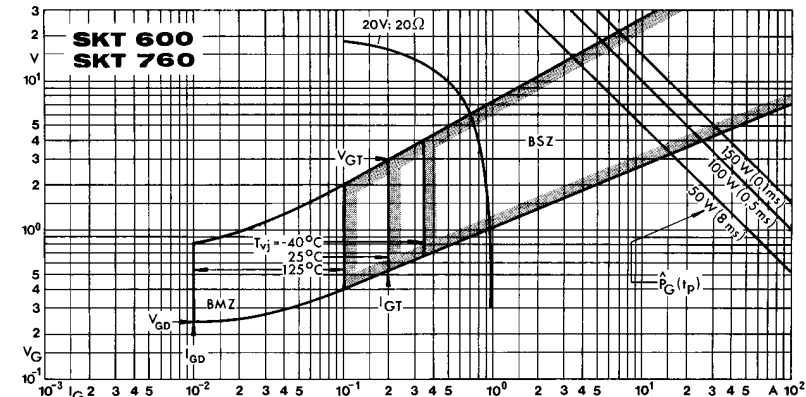


Fig. 9 Gate trigger characteristics